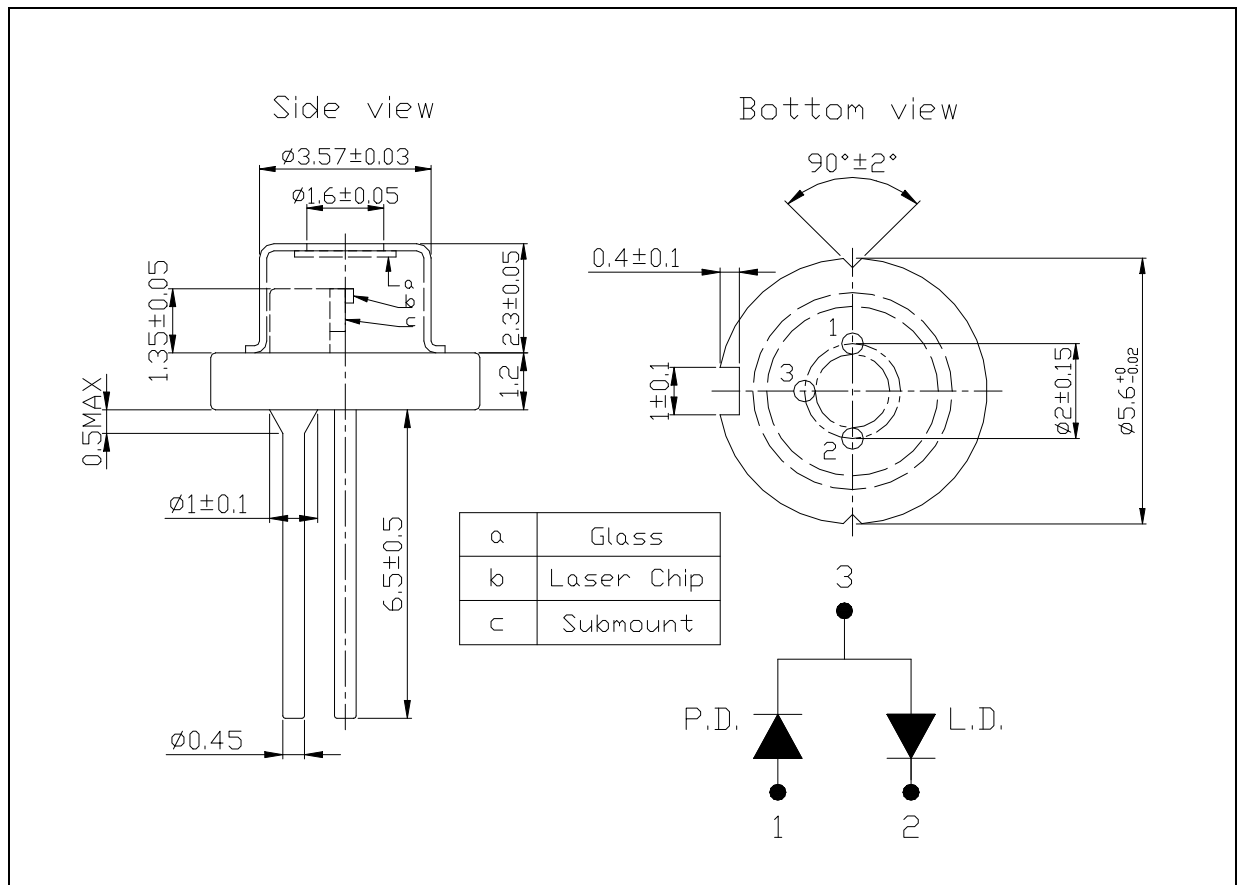


808nm IR Laser Diode RLD80802001

■ Specifications

(1) Device: Laser Diode

■ External dimensions(Unit : mm) TO-18(ϕ 5.6mm),With Pb free glass cap, PD



■ Absolute Maximum Ratings($T_c=25^\circ\text{C}$)

Parameter	Ratings	Unit
Optical Output	200	mW
Operating Temperature	-10 ~ 50	$^\circ\text{C}$
Storage Temperature	-15 ~ 85	$^\circ\text{C}$
Soldering temperature	260	$^\circ\text{C}$

Absolute Maximum Ratings($T_c=25^\circ\text{C}$)

Paramter	Symble	Unit	Specification			Others
			min	type	max	
Wavelength	λ	nm	805	808	811	
Spectrum width (FWHM)	$\Delta\lambda$	nm		2.5	4.0	
Output power (CW)	P_0	mW	200			Kink-free
Threshold Current	I_{th}	mA		50	70	
Forward current	I_{op}	mA		210	220	$P_0=200\text{mW}$
Forward voltage	V_{op}	V		1.9	2.1	$P_0=200\text{mW}$
Sloping Efficiency	η_D	mW/mA	1.0	1.1	—	
Operating temperature	T_{op}	$^\circ\text{C}$	- 10—50			
work life	t	Hr	10000	—	—	25°C
Beam divergence (FWHM)	B	$\theta_{\perp} \times \theta_{\parallel}$	—	$38^\circ \times 10^\circ$	—	
Emit Width		μm		30		
Chip Width	W	μm		300		Or $500\mu\text{m}$
Cavity Length	L	μm		500		
Chip Thickness	T	μm	100	110	120	Or $150\mu\text{m}$